

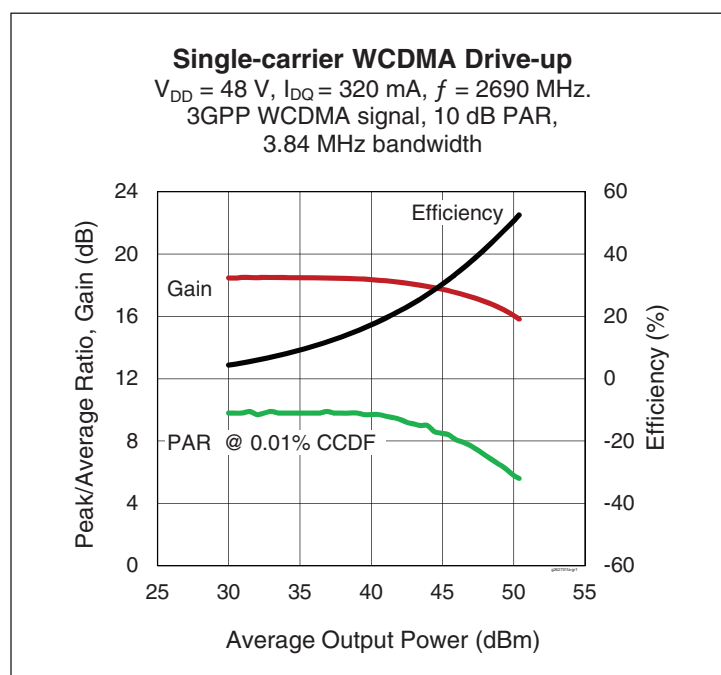
# GTVA262701FA

## Thermally-Enhanced High Power RF GaN on SiC HEMT 270 W, 48 V, 2620 – 2690 MHz

### Description

The GTVA262701FA is a 270-watt GaN on SiC high electron mobility transistor (HEMT) for use in multi-standard cellular power amplifier applications. It features input matching, high efficiency, and a thermally-enhanced surface-mount package with earless flange.

GTVA262701FA  
Package H-87265J-2



### Features

- GaN on SiC HEMT technology
- Input matched
- Typical pulsed CW performance: 10  $\mu\text{s}$  pulse width, 10% duty cycle, 2690 MHz, 48 V
  - Output power at  $P_{3dB} = 270\text{ W}$
  - Efficiency = 66%
  - Gain = 18.1 dB
- Human Body Model Class 1B (per ANSI/ESDA/JEDEC JS-001)
- Capable of handling 10:1 VSWR @ 48 V, 60 W (WCDMA) output power
- Pb-free and RoHS compliant

### RF Characteristics

#### Single-carrier WCDMA Specifications (tested in Wolfspeed production test fixture)

$V_{DD} = 48\text{ V}$ ,  $I_{DQ} = 320\text{ mA}$ ,  $P_{OUT} = 60\text{ W}$  avg,  $f = 2690\text{ MHz}$ , 3GPP signal, channel bandwidth = 3.84 MHz, peak/average = 10 dB @ 0.01% CCDF

Characteristic	Symbol	Min	Typ	Max	Unit
Gain	$G_{ps}$	16.5	17	—	dB
Drain Efficiency	$\eta_D$	40	42	—	%
Adjacent Channel Power Ratio	ACPR	—	-28	-27	dBc
Output PAR @ 0.01% CCDF	OPAR	5.5	6.2	—	dB

All published data at  $T_{CASE} = 25^\circ\text{C}$  unless otherwise indicated

ESD: Electrostatic discharge sensitive device—observe handling precautions!

## DC Characteristics

Characteristic	Conditions	Symbol	Min	Typ	Max	Unit
Drain-source Breakdown Voltage	$V_{GS} = -8\text{ V}$ , $I_D = 10\text{ mA}$	$V_{(BR)DSS}$	150	—	—	V
Drain-source Leakage Current	$V_{GS} = -8\text{ V}$ , $V_{DS} = 10\text{ V}$	$I_{DSS}$	—	—	4.5	mA
Gate Threshold Voltage	$V_{DS} = 10\text{ V}$ , $I_D = 32\text{ mA}$	$V_{GS(th)}$	-3.8	-3.0	-2.3	V

## Recommended Operating Conditions

Parameter	Conditions	Symbol	Min	Typ	Max	Unit
Operating Voltage		$V_{DD}$	0	—	55	V
Gate Quiescent Voltage	$V_{DS} = 50\text{ V}$ , $I_D = 320\text{ mA}$	$V_{GS(Q)}$	—	-3.0	—	V

## Absolute Maximum Ratings

Parameter	Symbol	Value	Unit
Drain-source Voltage	$V_{DSS}$	125	V
Gate-source Voltage	$V_{GS}$	-10 to +2	V
Gate Current	$I_G$	32	mA
Drain Current	$I_D$	12	A
Junction Temperature	$T_J$	225	°C
Storage Temperature Range	$T_{STG}$	-65 to +150	°C

Operation above the maximum values listed here may cause permanent damage. Maximum ratings are absolute ratings; exceeding only one of these values may cause irreversible damage to the component. Exposure to absolute maximum rating conditions for extended periods may affect device reliability. For reliable continuous operation, the device should be operated within the operating voltage range ( $V_{DD}$ ) specified above.

## Thermal Characteristics

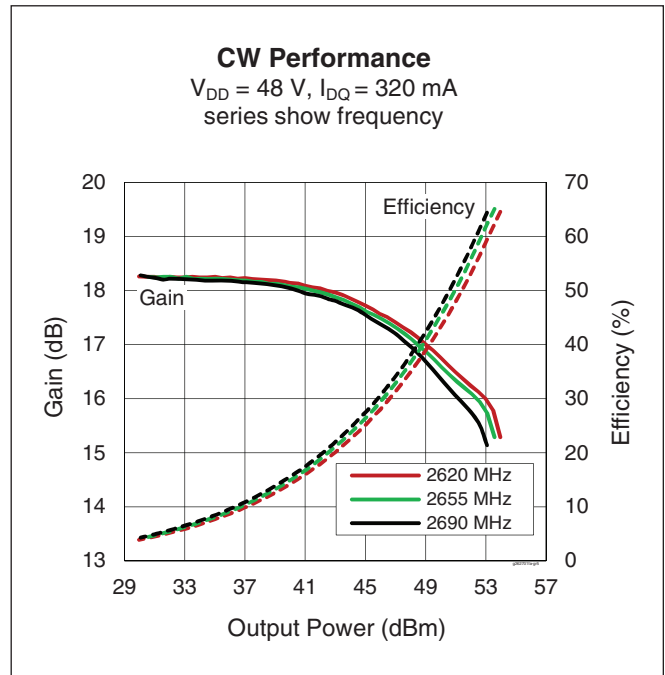
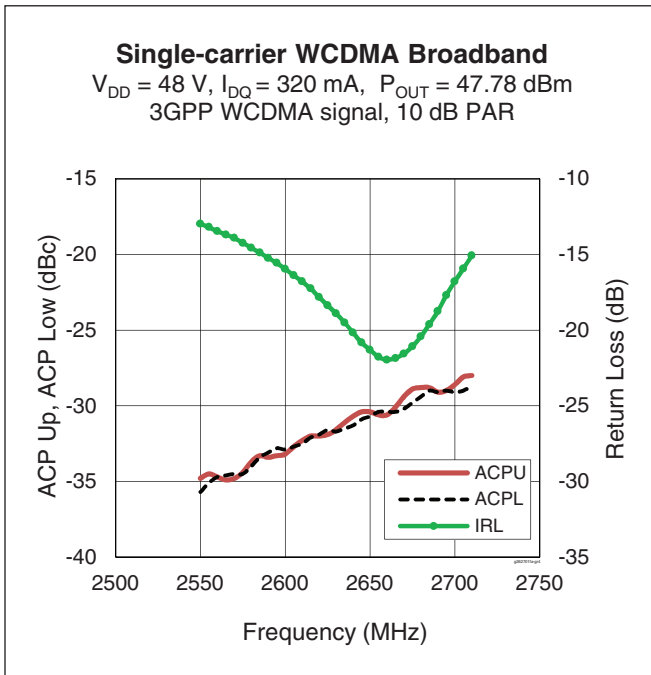
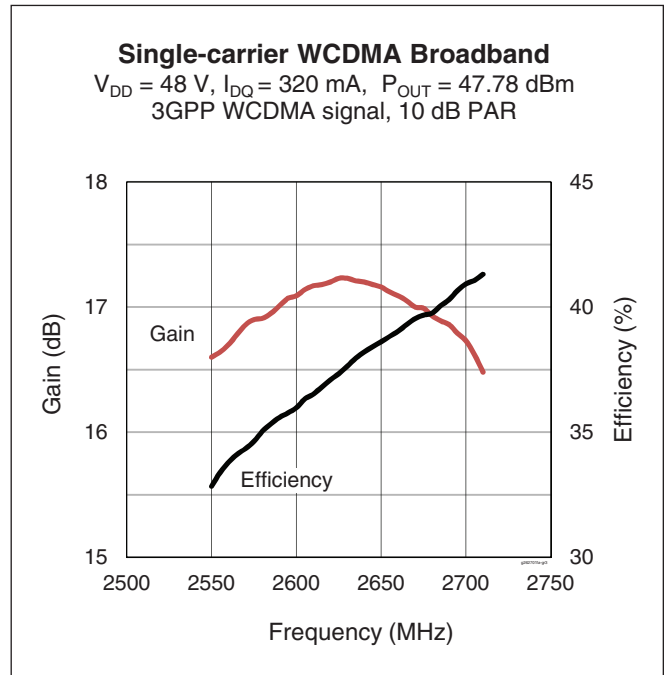
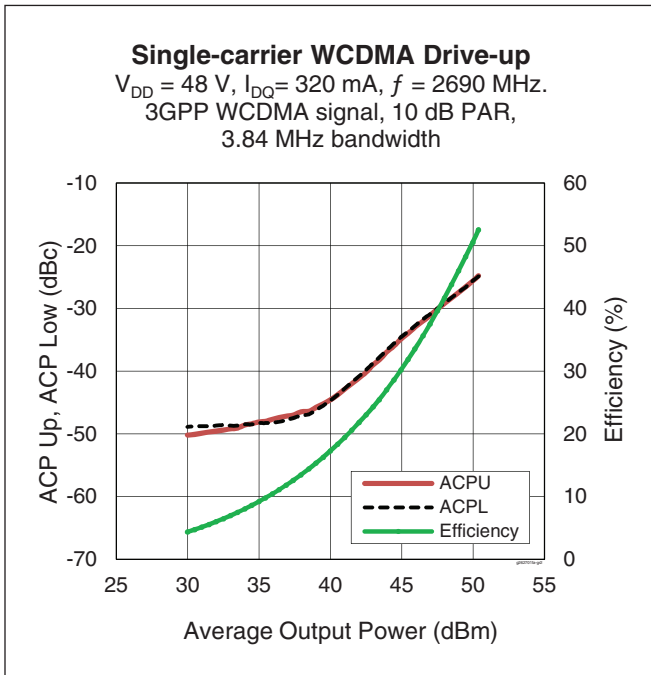
Characteristic	Symbol	Value	Unit
Thermal Resistance ( $T_{CASE} = 70\text{ °C}$ , 60 W (CW), $V_{DD} = 48\text{ V}$ , $I_{DQ} = 320\text{ mA}$ , 2690 MHz)	$R_{\theta JC}$	1.1	°C/W

## Ordering Information

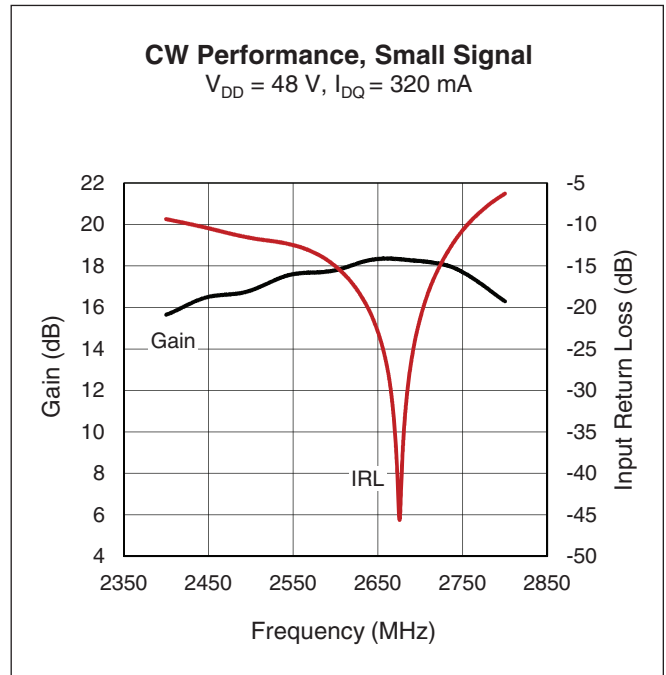
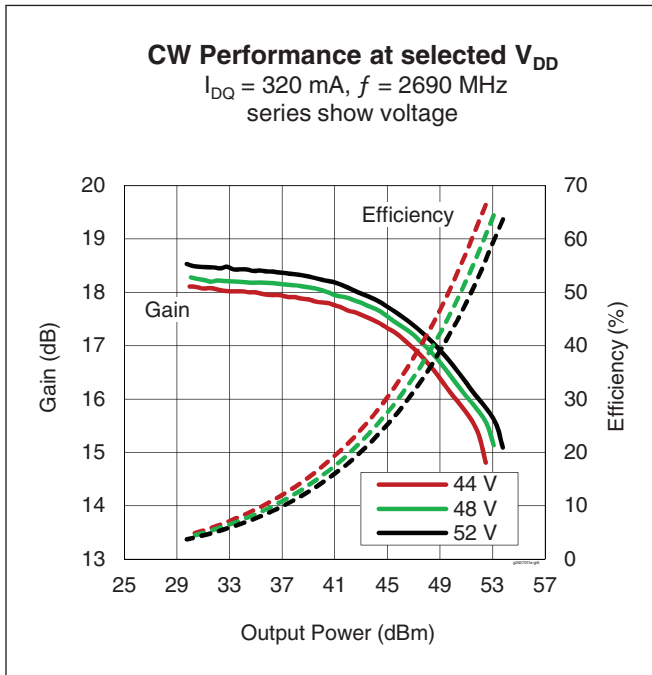
Type and Version	Order Code	Package	Shipping
GTVA262701FA V2 R0	GTVA262701FA-V2-R0	H-87265J-2	Tape & Reel, 50 pcs
GTVA262701FA V2 R2	GTVA262701FA-V2-R2	H-87265J-2	Tape & Reel, 250 pcs



**Typical Performance** (data taken in Wolfspeed production test fixture)



**Typical Performance (cont.)**



**Load Pull Performance**

Pulsed CW signal – 10  $\mu\text{sec}$ , 10% duty cycle; 48 V, 320 mA

Class AB			$P_{3dB}$									
			Max Output Power					Max Drain Efficiency				
Freq [MHz]	$Z_{source} [\Omega]$	$Z_{L\ 2f0} [\Omega]$	$Z_{load} [\Omega]$	Gain [dB]	$P_{3dB}$ [dBm]	$P_{3dB}$ [W]	$\eta_D$ [%]	$Z_{load} [\Omega]$	Gain [dB]	$P_{3dB}$ [dBm]	$P_{3dB}$ [W]	$\eta_D$ [%]
2620	6.90 – j4.0	1.4 + j4.3	2.24 – j3.80	15.2	54.71	296	62.3	1.95 – j1.91	17.45	52.89	194.5	75.1
2655	6.85 – j3.4	2.3 + j10	2.20 – j3.78	15.2	54.80	302	63.4	2.26 – j2.27	16.70	53.14	206.1	73.6
2690	5.90 – j4.8	1.7 + j8.3	2.12 – j3.74	15.2	54.78	301	65.1	1.80 – j2.00	16.80	52.65	184.1	75.7

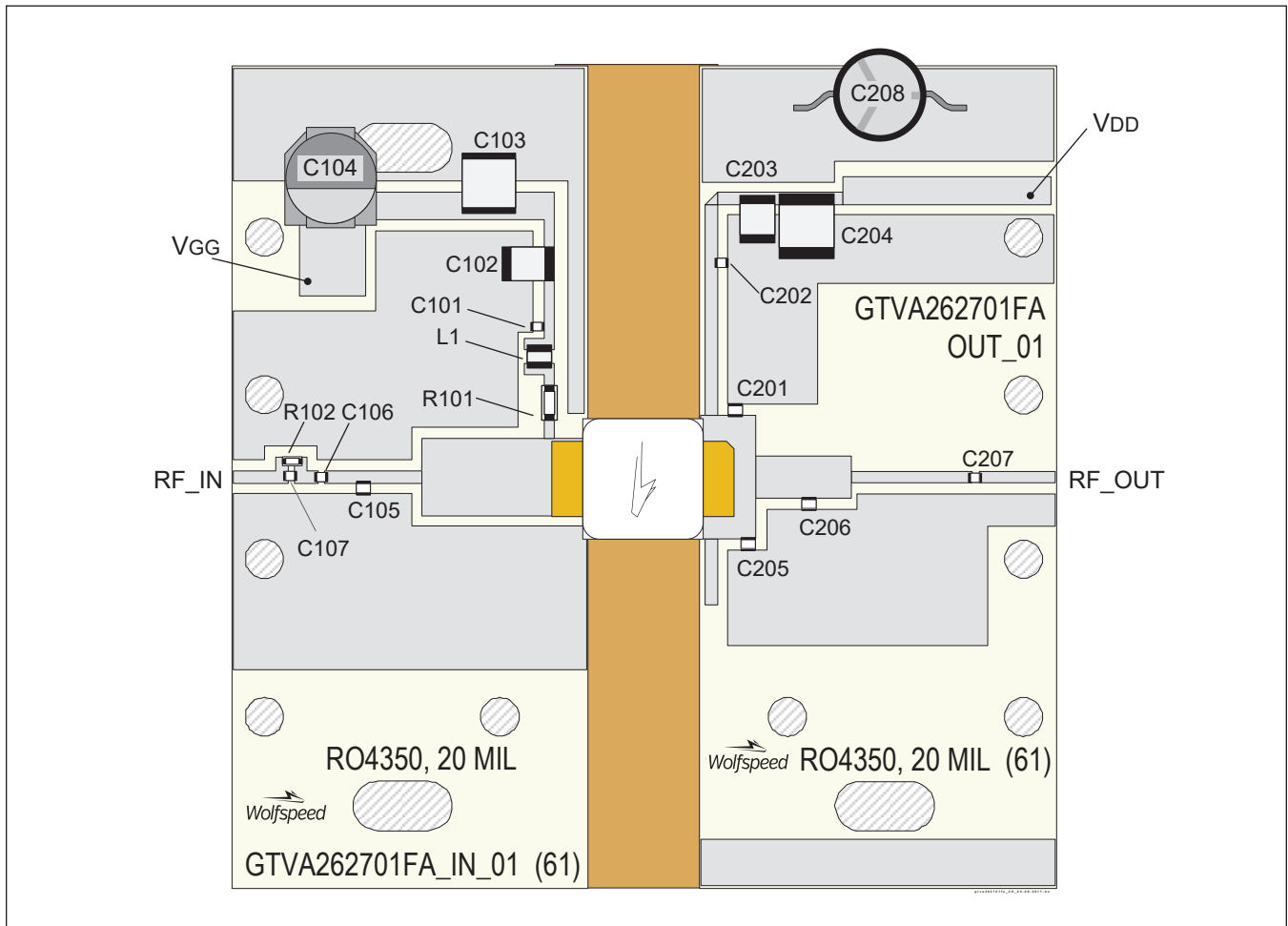


**Reference Circuit tuned for 2620 to 2690 MHz**

**Reference Circuit Assembly**

DUT	GTVA262701FA V2
Test Fixture Part No.	LTN/GTVA262701FA-V2
PCB	Rogers 4350, 0.508 mm [0.020"] thick, 2 oz. copper, $\epsilon_r = 3.66$

Find Gerber files for this test fixture on the WolfSpeed Web site at <http://www.wolfspeed.com/RF>



Reference circuit assembly diagram (not to scale)

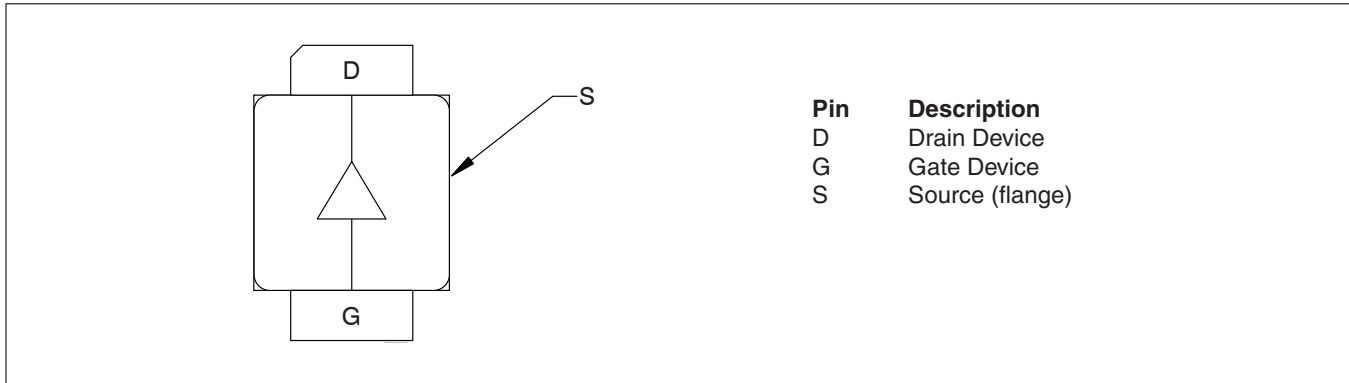


## Reference Circuit tuned for 2620 to 2690 MHz

### Components Information

Component	Description	Manufacturer	P/N
<b>Input</b>			
C101	Capacitor, 33 pF	ATC	ATC800A330JT250T
C102	Capacitor, 1 μF	TDK Corporation	C4532X7R2A105M230KA
C103	Capacitor, 10 μF	TDK Corporation	C5750X5R1H106K230KA
C104	Capacitor, 100 μF	Panasonic Electronic Components	EEV-HD1V101P
C105	Capacitor, 1.8 pF	ATC	ATC800A1R8CT250T
C106, C107	Capacitor, 12 pF	ATC	ATC800A120JT250T
L1	Inductor, 22 nH	ATC	0805WL220JT
R101	Resistor, 5.6 ohms	Panasonic Electronic Components	ERJ-8RQJ5R6V
R102	Resistor, 10 ohms	Panasonic Electronic Components	ERJ-3GEYJ100V
<b>Output</b>			
C201	Capacitor, 1.1 pF	ATC	ATC800A1R1CT250T
C202, C207	Capacitor, 12 pF	ATC	ATC800A120JT250T
C203	Capacitor, 1 μF	TDK Corporation	C4532X7R2A105M230KA
C204	Capacitor, 10 μF	TDK Corporation	C5750X5R1H106K230KA
C205	Capacitor, 0.9 pF	ATC	ATC800A0R9CT250T
C206	Capacitor, 0.4 pF	ATC	ATC800A0R4CT250T
C208	Capacitor, 220 μF	Panasonic Electronic Components	ECA-2AHG221

### Pinout Diagram (top view)



Lead connections for GTVA262701FA

Package Outline Specifications

